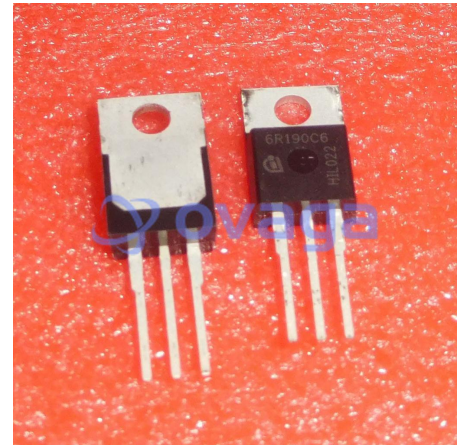


N-Channel MOSFETs (>500V...900V); Package: PG-TO220-3; VDS (max): 600.0 V;  
 Package: TO-220; RDS(ON) @ TJ=25°C VGS=10: 190.0 mOhm; ID(max) @ TC=25°C:  
 20.2 A; IDpuls (max): 59.0 A;

Manufacturers	<u>Infineon Technologies Corporation</u>
Package/Case	TO-220-3
Product Type	Transistors
RoHS	Green
Lifecycle	



Images are for reference only

Please submit RFQ for IPP60R190C6 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

## General Description

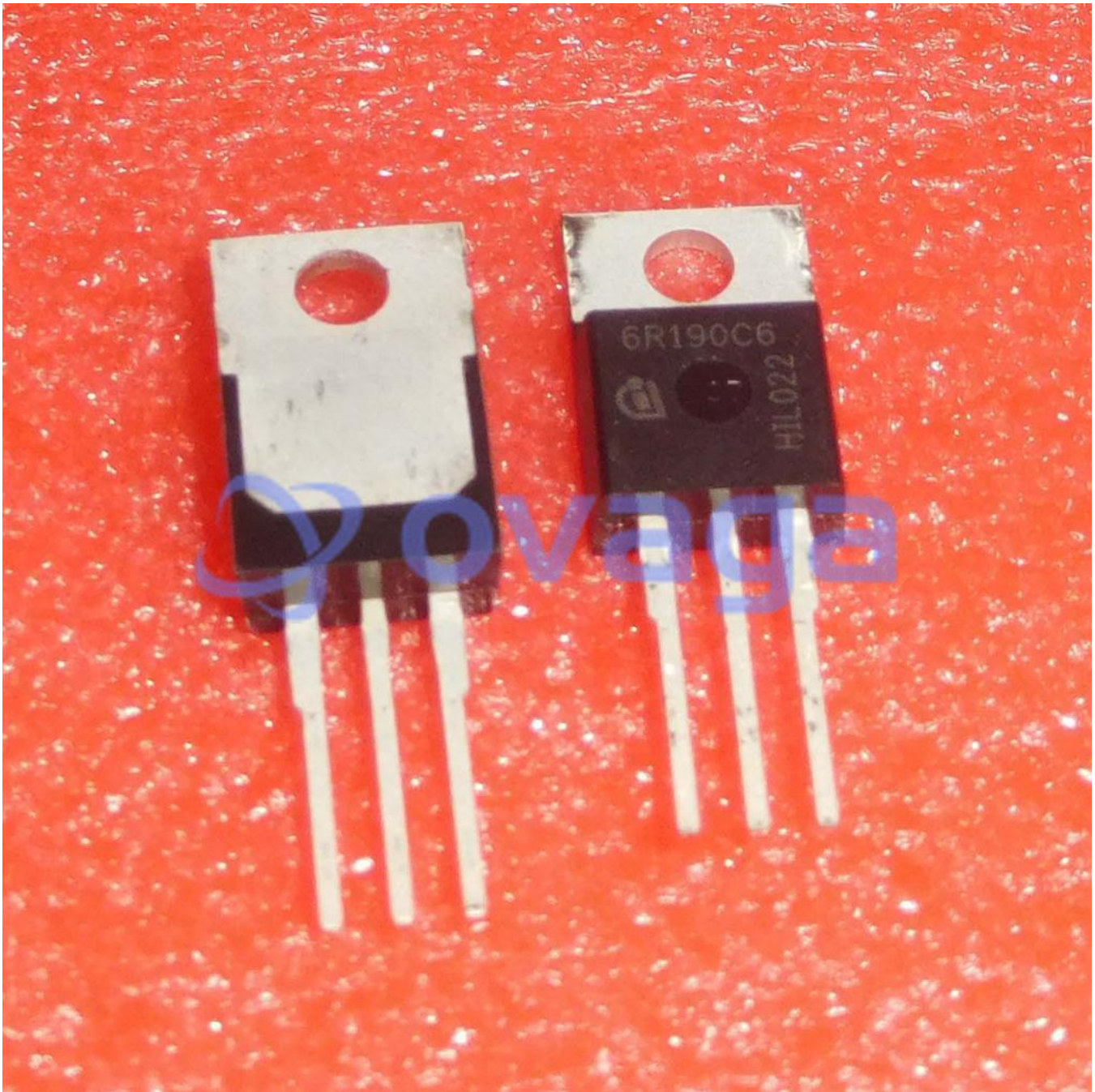
IPP60R190C6 is a power MOSFET (metal-oxide-semiconductor field-effect transistor) that is designed for high-voltage applications. It is manufactured by Infineon Technologies, a semiconductor company based in Germany.

### Features

- Drain-source voltage rating: 600V
- Continuous drain current: 24A
- Maximum power dissipation: 300W
- Low on-resistance: 190mOhm
- Fast switching performance

### Application

- Power supplies
- Motor drives
- Lighting systems
- Audio amplifiers
- Switching regulators



### Related Products



[IPP60R070CFD7](#)

Infineon Technologies Corporation  
TO-220-3



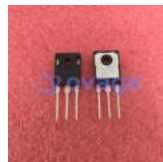
[IPB180N06S4-H1](#)

Infineon Technologies Corporation  
PG-TO263-7-3



[IPG20N04S4-12](#)

Infineon Technologies Corporation  
TDSON-8



[IPW65R080CFD](#)

Infineon Technologies Corporation  
TO-247



[IPD25N06S4L-30](#)

Infineon Technologies Corporation  
PG-TO252-3



[IPD180N10N3G](#)

Infineon Technologies Corporation  
TO-252



[IPP60R074C6](#)

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TO-220-3



[IPD70R1K4P7S](#)

Infineon Technologies Corporation  
TO252-3